PROCESS CP379X

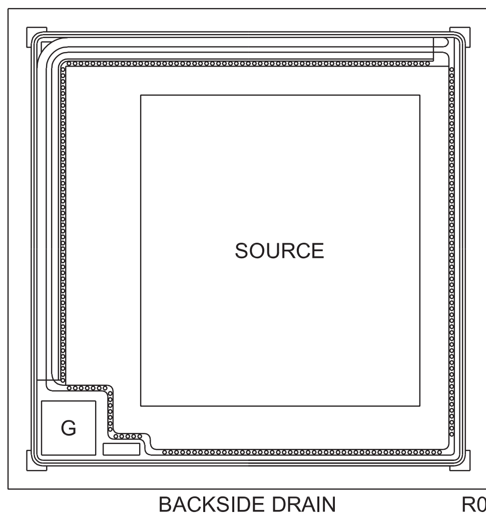
Small Signal MOSFET Transistor

N-Channel Enhancement-Mode Transistor Chip

PROCESS DETAILS

Die Size	31.5 x 31.5 MILS
Die Thickness	5.5 MILS
Gate Bonding Pad Area	3.9 x 3.9 MILS
Source Bonding Pad Area	19.3 x 21.3 MILS
Top Side Metalization	Al-Si - 35,000Å
Back Side Metalization	Ti/Ni/Ag - 2,000Å/3,000Å/20,000Å

GEOMETRY



BACKSIDE DRAIN R0

GROSS DIE PER 6 INCH WAFER
24,000

PRINCIPAL DEVICE TYPE
CMPDM7002AHC

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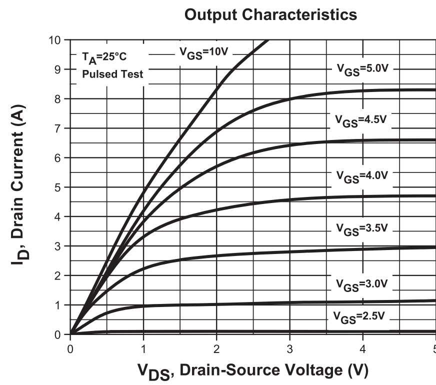
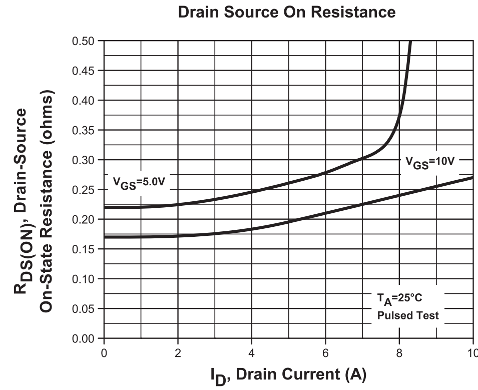
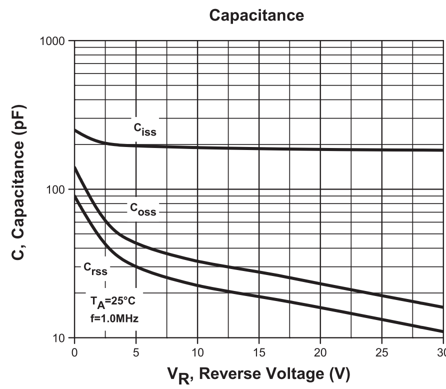
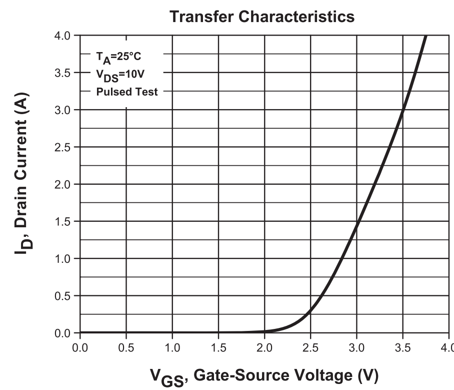
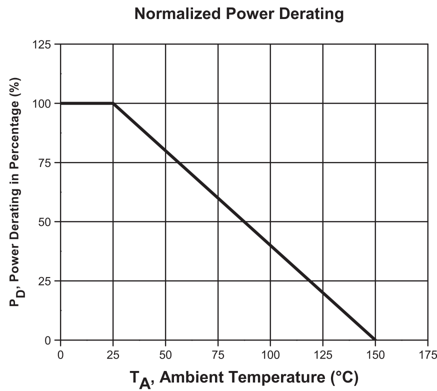
Typical Electrical Characteristics











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